

**In the Claims:**

Please cancel claims 1-11. Please amend claims 12, 17-19, 23, and 25. Please add new claims 26-29. The claims are as follows.

1-11. (Canceled)

12. (Currently amended) A transistor comprising:

- a) a transistor body formed on a substrate, the transistor body having a first vertical edge and a second vertical edge;
- b) a gate structure in direct mechanical contact with the transistor body first vertical edge;
- c) a body contact structure adjacent the transistor body second vertical edge and aligned with the gate structure, a top surface of the gate structure and a top surface of the body contact structure being coplanar, a bottom surface of the gate structure and a bottom surface of the body contact structure being coplanar;
- d) a bridge over the transistor body, the gate structure, and the body contact structure, the bridge electrically connecting the gate structure and the body contact structure; and
- e) source and drain regions in the transistor body on opposite ends of the transistor body.

13. (Original) The transistor of claim 12 wherein the gate structure comprises p-type material and wherein the body contact structure comprises n-type material.

14. (Original) The transistor of claim 12 wherein the gate structure comprises n-type material and

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wherein the body contact structure comprises p-type material.

15. (Original) The transistor of claim 12 wherein the transistor body comprises a portion of silicon of the silicon-on-insulator layer.

16. (Original) The transistor of claim 12 wherein the thickness of the transistor body between the gate structure and the body contact structure is less than one-third of the length of the gate structure.

17. (Currently amended) A transistor comprising:

a) a transistor body formed on a substrate, the transistor body having a first vertical edge and a second vertical edge;

b) a gate structure adjacent the transistor body first vertical edge;

c) a body contact structure adjacent the transistor body second vertical edge and aligned with the gate structure;

d) a bridge over the transistor body, the gate structure, and the body contact structure, the bridge electrically connecting the gate structure and the body contact structure;

e) source and drain regions in the transistor body on opposite ends of the transistor body;

f) a gate dielectric between the transistor body first edge and the gate structure; and

g) a diffusion barrier between the transistor body second edge and the body contact structure.

18. (Currently amended) The transistor of claim 12 wherein the transistor body comprises source and drain implants into the transistor body, the implants aligned with the edges of the body contact structure and the gate structure.

19. (Currently amended) A transistor comprising:

- a) a transistor body formed on a substrate, the transistor body having a first vertical edge and a second vertical edge;
- b) a gate structure adjacent the transistor body first vertical edge;
- c) a body contact structure adjacent the transistor body second vertical edge and aligned with the gate structure;
- d) a bridge over the transistor body, the gate structure, and the body contact structure, the bridge electrically connecting the gate structure and the body contact structure; and
- e) source and drain regions in the transistor body on opposite ends of the transistor body, wherein the transistor body comprises widened end portions that are insulated from the gate structure and the body contact structure.

20. (Original) The transistor of claim 12 wherein the transistor body first edge is opposite the transistor body second edge and wherein the transistor body first edge and transistor body second edge are substantially perpendicular to a top surface of the substrate.

21. (Original) A dynamic threshold complimentary metal oxide semiconductor field effect transistor comprising:

a) a transistor body, the transistor body formed from a silicon layer formed above an insulator layer, the transistor body having a first vertical edge and a second vertical edge, wherein the transistor body first edge and the transistor body second edge are opposite each other and substantially perpendicular to the insulator layer, thereby defining a fin-type transistor body;

b) a gate dielectric layer formed on the transistor body first edge;

c) a body contact native oxide layer formed on the transistor body second edge;

d) a gate structure formed on the gate dielectric layer adjacent to the transistor body first edge, the gate structure comprising p-type polysilicon; and

e) a body contact structure formed on the body contact native oxide layer aligned to the gate structure and adjacent to the transistor body second edge, the body contact structure comprising n-type polysilicon.

22. (Original) A dynamic threshold complimentary metal oxide semiconductor field effect transistor of claim 21 wherein the gate structure comprises n-type polysilicon and the body contact structure comprises p-type polysilicon.

23. (Currently amended) The dynamic threshold complimentary metal oxide semiconductor field effect transistor of claim 21 wherein the transistor body comprises a substantially uniform dopant concentration density in the source and drain regions.

24. (Original) The dynamic threshold complimentary metal oxide semiconductor field effect transistor of claim 23 wherein the substantially uniform dopant concentration density is formed

by performing a plurality of angled implants into the transistor body.

25. (Currently amended) The dynamic threshold complimentary metal oxide semiconductor field effect transistor of claim 21 further comprising a metal silicide bridge over the transistor body to electrically couple the gate structure to the body contact structure.

26. (New) The transistor of claim 12, wherein the bridge is in direct mechanical contact with the gate structure and the body contact structure.

27. (New) The transistor of claim 12, further comprising an insulator on the transistor body and in direct mechanical contact with a top edge of the transistor body, wherein the insulator is disposed between the gate structure and the body contact structure, and wherein the bridge is in direct mechanical contact with the insulator.

28. (New) The transistor of claim 27, wherein a top surface of the insulator is coplanar with the top surface of the gate structure and the top surface of the body contact structure.

29. (New) The transistor of claim 27, wherein the bridge is in direct mechanical contact with the gate structure and the body contact structure.